TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7WH241FU,TC7WH241FK

## Dual Bus Buffer Non Inverted, 3-State Outputs

The TC7WH241 is an advanced high speed CMOS DUAL BUS BUFFERS fabricated with silicon gate CMOS technology.

They schieve the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. The 7WH241 is an inverting 3-state buffer having two active-low output enables.

This device is designed to be used with 3-state memory address drivers, etc.

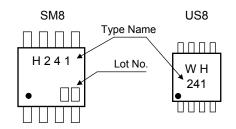
An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage.

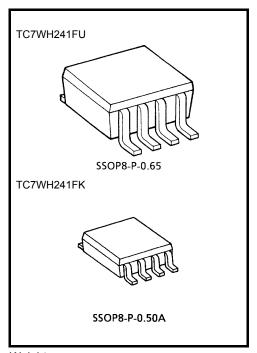
This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

# Features

- High speed:  $t_{pd}$  = 3.6 ns (typ.) at V<sub>CC</sub> = 5 V
- Low power dissipation:  $I_{CC} = 2 \mu A (max)$  at  $Ta = 25^{\circ}C$
- High noise immunity:  $V_{\text{NIH}} = V_{\text{NIL}} = 28\% V_{\text{CC}}$  (min)
- 5.5-V Tolerant inputs.
- Balanced propagation delays:  $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range:  $V_{CC}$  (opr) = 2~5.5 V
- Low Noise : V<sub>OLP</sub> = 0.8 V (max.)

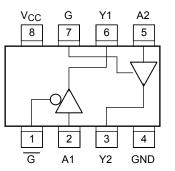
#### Marking





Weight SSOP8-P-0.65: 0.02 g (typ.) SSOP8-P-0.50A: 0.01 g (typ.)

#### Pin Assignment (top view)



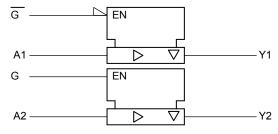
# Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	IIК	-20	mA
Output diode current	I <sub>OK</sub>	±20	mA
DC output current	IOUT	±25	mA
DC V <sub>CC</sub> /ground current	ICC	±50	mA
Power dissipation	D-	300 (SM8)	mW
	PD	200 (US8)	
Storage temperature	T <sub>stg</sub>	-65~150	°C
Lead temperature (10 s)	ΤL	260	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Logic Diagram



#### Truth Table

INPUTS			OUTPUTS			
G	G	А	Ŷ			
L	Н	L	L			
L	Н	Н	Н			
Н	L	Х	Z			

X : Don't Care

Z : High Impedance

# **Operating Ranges**

Characteristics	Symbol	Rating	Unit	
Supply voltage	V <sub>CC</sub>	2.0~5.5	V	
Input voltage	V <sub>IN</sub>	0~5.5	V	
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V	
Operating temperature	T <sub>opr</sub>	-40~85	°C	
Input rise and fall time	dt/dv	0~100 (V_{CC} = 3.3 $\pm$ 0.3 V)	ns/V	
	avav	0~20 (V <sub>CC</sub> = 5 $\pm$ 0.5 V)	115/ V	

# **Electrical Characteristics**

#### **DC Characteristics**

				7	۲a = 25°0	2	Ta = -4	0~85°C		
Characteristics Symbol Test Condition		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit		
		_		2.0	1.50			1.50		v
High-level input voltage	VIH			3.0~ 5.5	V <sub>CC</sub> × 0.7	_	_	V <sub>CC</sub> × 0.7	_	
				2.0	_		0.50		0.50	V
Low-level input voltage	Low-level input voltage V <sub>IL</sub> —		3.0~ 5.5	_		V <sub>CC</sub> × 0.3	_	$V_{CC} \times 0.3$		
	Vон	VIN = VIH or VIL	I <sub>OH</sub> = -50 μA	2.0	1.9	2.0		1.9	_	
				3.0	2.9	3.0	_	2.9	_	V
High-level output voltage				4.5	4.4	4.5	_	4.4	_	
			I <sub>OH</sub> = -4 mA	3.0	2.58		_	2.48	_	
			I <sub>OH</sub> = -8 mA	4.5	3.94		_	3.80	_	
	Vol	VIN = VIH or VIL	I <sub>OL</sub> = 50 μA	2.0	_	0.0	0.1	_	0.1	
				3.0	_	0.0	0.1	_	0.1	
Low-level output voltage				4.5		0.0	0.1	—	0.1	V
			$I_{OL} = 4 \text{ mA}$	3.0		_	0.36	—	0.44	
			I <sub>OL</sub> = 8 mA	4.5		_	0.36	—	0.44	
3-State Output Off-State Current	I <sub>OZ</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or } GND$		5.5	_	_	0.25	_	2.50	μΑ
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0~ 5.5	_	_	±0.1	_	±1.0	μΑ
Quiescent supply current	ICC	$V_{IN} = V_{CC}$ or GND		5.5		_	2.0	_	20.0	μA

# AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol Test Condition				Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min.	Тур.	Max.	Min.	Max.	Unit
Propagation Delay Time	t <sub>pLH</sub>		$3.3\pm0.3$	15	_	5.3	7.5	1.0	9.0	ns
				50	_	7.8	11.0	1.0	12.5	
	t <sub>pHL</sub>		5.0 ± 0.5	15	_	3.6	5.5	1.0	6.5	
			$5.0 \pm 0.5$	50	_	5.1	7.5	1.0	8.5	
		$R_L = 1 kΩ = 5.0 \pm 0.5$	$\textbf{3.3}\pm\textbf{0.3}$	15	_	6.6	10.6	1.0	12.5	• ns
3-State Output	$t_{pZL}$ $t_{pZH}$ $R_L = 1k\Omega$			50	_	9.1	14.1	1.0	16.0	
Enable Time			50.05	15	_	4.7	7.3	1.0	8.5	
			50	_	6.2	9.3	1.0	10.5		
3-State Output Disable Time	t <sub>pLZ</sub>	$R_L = 1k\Omega$	$3.3\pm 0.3$	50	_	10.3	14.0	1.0	16.0	ns
	t <sub>pHZ</sub>		$5.0\pm0.5$	50	_	6.7	9.2	1.0	10.5	115
Output to Output	tos <sub>LH</sub>	(Nata 1)	$3.3\pm 0.3$	50	_	_	1.5	_	1.5	ns
Skew	tos <sub>HL</sub>	(Note 1)	$5.0\pm0.5$	50	_	_	1.0	_	1.0	115
Input Capacitance	C <sub>IN</sub>				_	4	10	_	10	pF
Output Capacitance	C <sub>I/O</sub>				_	6	_	_	_	pF
Power Dissipation Capacitance (Note 2)	C <sub>PD</sub>				_	17		_	_	pF

Note 1: Parameter guaranteed by design.

tosLH = |tpLHm - tpLHn|, tosHL = |tpHLm - tpHLn|

Note 2:C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

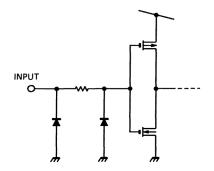
Average operating current can be obtained by the equation :

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$ 

#### Noise Characteristics (Ta = $25^{\circ}$ C, input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition	V <sub>CC</sub> (V)	Тур.	Limit	Unit
Quiet output maximum dynamic $V_{OL}$	V <sub>OLP</sub>	C <sub>L</sub> = 50 pF	5.0	0.3	0.8	V
Quiet output minimum dynamic $V_{OL}$	V <sub>OLV</sub>	C <sub>L</sub> = 50 pF	5.0	-0.3	-0.8	V
Minimum high level dynamic input voltage	V <sub>IHD</sub>	C <sub>L</sub> = 50 pF	5.0		3.5	V
Maximum low level dynamic input voltage	V <sub>ILD</sub>	C <sub>L</sub> = 50 pF	5.0		1.5	V

# Input Equivalent Circuit

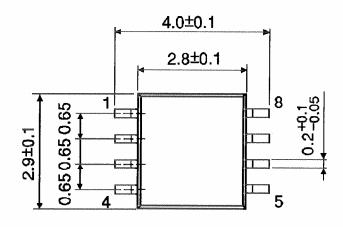


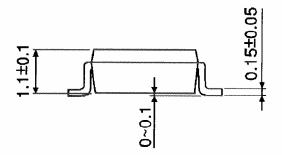
# **TOSHIBA**

# **Package Dimensions**

#### SSOP8-P-0.65

Unit : mm



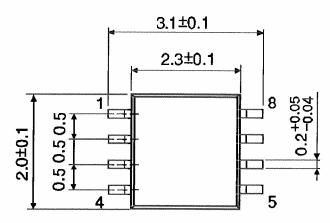


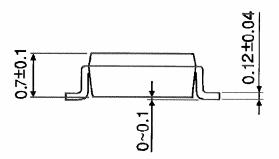
Weight: 0.02 g (typ.)

# **Package Dimensions**

SSOP8-P-0.50A

Unit : mm





Weight: 0.01 g (typ.)

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20070701-EN GENERAL

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